

## Si APD

#### S15414 series

# High-speed, compact Si APD that does not require temperature adjustment

The S15414 series is a gain-stabilized APD (GS APD) with a built-in temperature compensation function inside the sensor. This realizes constant gain without the need for temperature adjustment. It is suitable for laser monitors of optical rangefinders used in a wide range of applications, from consumer to industrial.

#### Features

- **■** Built-in temperature compensation function
- Compact package: 2.0 × 1.8 × 0.85<sup>t</sup> mm
- Peak sensitivity wavelength: 800 nm (M=50)
- → High-speed response: Cutoff frequency=1.2 GHz typ. (S15414-02, λ=800 nm, M=50)

#### Applications

Optical rangefinders

#### Structure

Parameter	S15414-02	S15414-05	Unit	
Photosensitive area*1	φ0.2	φ0.5	mm	
Package	Glass epoxy			
Seal material	Silicone resin			

<sup>\*1:</sup> Area in which a typical gain can be obtained

#### **■** Absolute maximum ratings

Parameter	Symbol	Specification	
Anode reverse current (DC)	IR anode max	0.1	mA
Forward current	IF max	10	mA
Operating temperature*2	Topr	-30 to +105	°C
Storage temperature*2	Tstg	-40 to +105	°C
Soldering temperature	Tsol	260 (3 times)*3	°C

<sup>\*2:</sup> No dew condensation

When there is a temperature difference between a product and the surrounding area in high humidity environments, dew condensation may occur on the product surface. Dew condensation on the product may cause deterioration in characteristics and reliability.

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

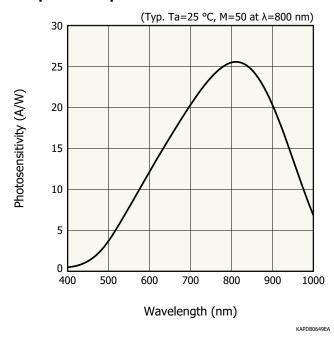
<sup>\*3:</sup> Reflow soldering, JEDEC J-STD-020 MSL 2a, see P.5

#### **■** Electrical and optical characteristics (Ta=25 °C, unless otherwise noted)

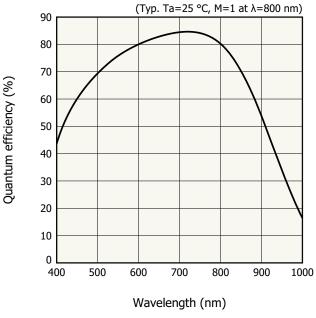
Dayamatar	Cumbal	Condition	S15414-02			S15414-05			l lmit
Parameter	Symbol	Condition	Min.	Тур.	Max.	Min.	Тур.	Max.	Unit
Spectral response range λ			400 to 1000				nm		
Peak sensitivity wavelength	λр		-	800	-	-	800	-	nm
Photosensitivity	S	λ=800 nm, M=1	-	0.52	-	-	0.52	-	A/W
Quantum efficiency	QE	λ=800 nm, M=1	-	80	-	-	80	-	%
Operating reverse voltage	Vop	Gain-stabilized mode operation*4	140 + 0.63 × (Ta opr -25)*5	-	-	140 + 0.63 × (Ta opr -25)*5	-	-	V
Temperature coefficient of operating reverse voltage ΔTVop			-	0.63	-	-	0.63	-	V/°C
Dark current ID Gain		Gain-stabilized mode operation*4	-	15	150	-	30	300	pА
Dark current temperature coefficient	ature ΔTID M=50		-	1.1	-	-	1.1	-	times/°C
Cutoff frequency	toff frequency fc $M=50$ , RL= $50 \Omega$ $\lambda=800$ nm, -3 dB		-	1.2	-	-	1.0	-	GHz
Terminal capacitance Ct M=50, f=1 MHz		M=50, f=1 MHz	-	0.6	-	-	1.4	-	pF
Excess noise figure $x$ M=50, $\lambda$ =		M=50, λ=800 nm	-	0.3	-	-	0.3	-	-
$\begin{array}{c c} \text{Gain} & \text{M} & \begin{array}{c} \text{Gain-stabilized mode} \\ \lambda = 800 \text{ nm} \end{array}$		Gain-stabilized mode operation*4, $\lambda$ =800 nm	40	50	60	40	50	60	-
Gain control range	-	λ=800 nm	-	30 to 100	-	-	30 to 100	-	-

<sup>\*4:</sup> Apply bias voltage to anode. IR anode limit=10  $\mu\text{A}$ , guard pin=GND

#### - Spectral response



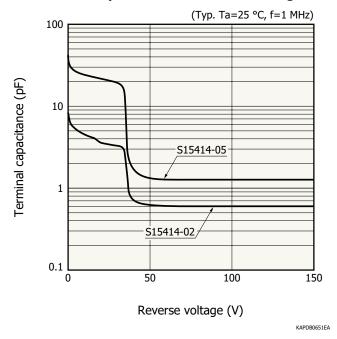
#### - Quantum efficiency vs. wavelength



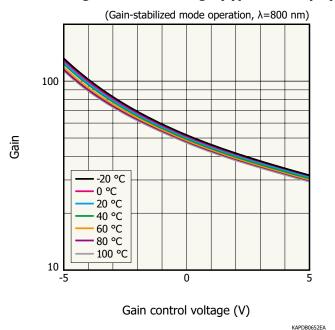
KAPDB0650EA

<sup>\*5:</sup> Ta opr=assumed maximum operating temperature

#### Terminal capacitance vs. reverse voltage

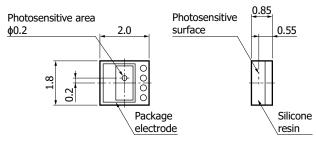


#### **Gain vs. gain control voltage (typical example)**

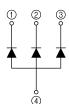


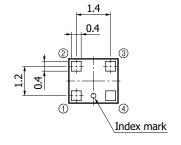
#### Dimensional outlines (unit: mm)

#### S15414-02



Tolerance unless otherwise noted:  $\pm 0.2$  Chip position accuracy with respect to package electrode pattern center: X, Y  $\leq \pm 0.2$ 

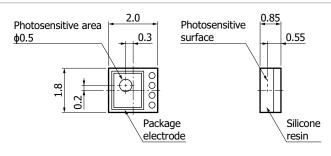


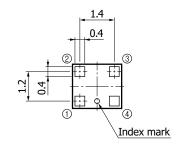


1	Gain control	Gain control voltage input (connect to GND)
2	Output	APD output
3	Guard	Leakage current output (connect to GND)
4	Anode	Bias voltage input

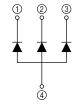
KAPDA0229EA

#### S15414-05





Tolerance unless otherwise noted:  $\pm 0.2$  Chip position accuracy with respect to package electrode pattern center: X, Y  $\leq \pm 0.2$ 



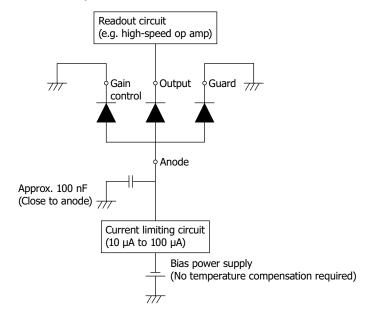
1	Gain control	Gain control voltage input (connect to GND)
2	Output	APD output
3	Guard	Leakage current output (connect to GND)
4	Anode	Bias voltage input

KAPDA0230EA

#### Recommended land pattern

# NAPPOOLISSEA

#### - Connection example



- $\cdot$  Connection to a bias power supply and a current limiting circuit are essential.
- The gain can be controlled by applying a voltage to the gain pin.
- · We recommend connecting a capacitor near the anode pin to stabilize the bias voltage.

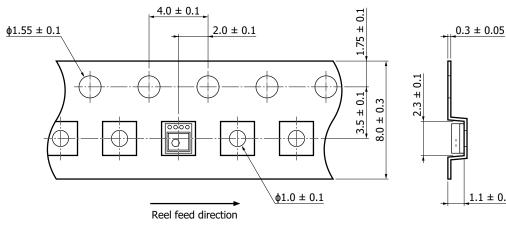
KAPDC0137EB

#### Standard packing specifications

■ Reel (conforms to JEITA ET-7200)

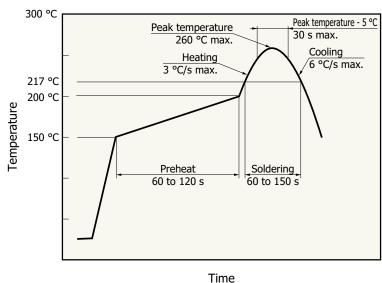
Appearance Hub diameter		Tape width	Material	Electrostatic characteristics	
φ180 mm	ф60 mm	8 mm	PS	Conductive	

■ Embossed tape (unit: mm, material: PS, conductive)



- Packing quantity 1000 pcs/reel
- Packing state Reel and desiccant in moisture-proof packaging (vacuum-sealed)

#### Recommended reflow soldering conditions



· After unpacking, store in an environment at a temperature of 30 °C or less and a humidity of 60% or less, and perform reflow soldering within 4 weeks.

 $1.1 \pm 0.1$ 

KAPDC0139EA

· The effect that the product receives during reflow soldering varies depending on the circuit board and reflow oven that are used. When you set reflow soldering conditions, check that problems do not occur in the product by testing out the conditions in advance.

KMPDB0405EC

#### Si APD

#### S15414 series

#### Baking

If 12 months have passed without unpacking or the above storage period has passed after unpacking, perform baking before reflow soldering to dehumidify. For the baking, refer to "Precautions / Surface mount type products" in the related information.

- Recommended baking conditions
- · Temperature: 150 °C, 3 hours, up to twice

Note: When you set baking conditions, check that problems do not occur in the product by testing out the conditions in advance.

#### Related information

www.hamamatsu.com/sp/ssd/doc\_en.html

- Precautions
- Disclaimer
- Precautions / Surface mount type products
- Catalogs
- · Technical note / Si APD

The content of this document is current as of June 2025.

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### MAMA

www.hamamatsu.com

Optical Semiconductor Sales, HAMAMATSU PHOTONICS K.K.

1126-1 Ichino-cho, Chuo-ku, Hamamatsu City, Shizuoka Pref., 435-8558 Japan, Telephone: (81)53-434-3311, Fax: (81)53-434-5184

11.26-1 ICHINO-CRIO, CRUO-KU, Hamamatsu City, Shizuoka Pret, 435-8536 Japan, Telephone: (81)53-4344-3311, FaX: (81)53-4344-3164

U.S.A. HAMAMATSU CRRORATION: 360 Footbill Road, Bridgewater, NJ 08807, U.S.A., Telephone: (1)908-231-960, Fax: (1)908-231-1218

Germany: HAMAMATSU PHOTONICS DEUTSCHLAND GMBH: Arzbergerst. 10, 82211 Herrsching am Ammersee, Germany, Telephone: (49)8152-375-0, Fax: (49)8152-265-8 E-mail: info@hamamatsu.de

France: HAMAMATSU PHOTONICS FRANCE S.A.R.L.: 19 Rue du Saule Trapu, Parc du Moulin de Massy, 91882 Massy Cedex, France, Telephone: (49)8152-375-0, Fax: (33)1 69 53 71 10 E-mail: info@hamamatsu.fr

United Kingdom: HAMAMATSU PHOTONICS UK LIMITED: 2 Howard Court, 10 Tewin Road, Welwyn Garden City, Hertfordshire, AL7 18W, UK, Telephone: (44)1707-294888, Fax: (44)1707-325777 E-mail: info@hamamatsu.se

United Kingdom: HAMAMATSU PHOTONICS NRDEN AB: Torshamningatan 35, 16440 Kista, Sweden, Telephone: (46)8-509-031-01. Fax: (46)8-509-031-01. E-mail: info@hamamatsu.se

Laly: HAMAMATSU PHOTONICS TALIA S.R.L.: Strada della Moia, 1 int. 6 20044 Arses (Milano), Italy, Helphone: (39)02-93 58 17 31, Fax: (39)02-93 58 17 41 E-mail: info@hamamatsu.ti. China: HAMAMATSU PHOTONICS (CHINA) CO., LTD: 151-1, No.101, Section 2, Gongdao Sth Road, East, Hamamatsu.de (Milano), Ltaly, Section 2, Gongdao Sth Road, East, S.H. Shendou City, Shoode, Talwan: HAMAMATSU PHOTONICS TALIA S.F.1, No.101, Section 2, Gongdao Sth Road, East, S.H. Shendou City, Shoode, Talwan: RAMAMATSU PHOTONICS TALIA S.F.1, No.101, Section 2, Gongdao Sth Road, East, S.H. Shendou City, Shoode, Talwan: RAMAMATSU PHOTONICS SALVAN CO., LTD: 13-11-1, No.101, Section 2, Gongdao Sth Road, East, Sh. Shendou City, Shoode, Talwan: RAMAMATSU PHOTONICS TALIA S.F.1, No.101, Section 2, Gongdao Sth Road, East, Sh. Shendou City, Shoode, Talwan: RAMAMATSU PHOTONICS SALVAN CO., LTD: 13-17-1, No.101, Section 2, Gongdao Sth Road, East, Sh. Shendou City, Shoode, Talwan: RAMAMATSU PHOTONICS SALVAN CO., LTD: 13-17-1, No.101, Section 2, Gongdao Sth Road, East, Sh. Sh